

IN THE SPECIFICATION

Please amend the specification as follows:

Replace the paragraph on page 4, between lines 1-17 of the specification with the following:

A preferred embodiment of the present invention will be explained in detail with reference to the accompanying drawing. FIG. 1 shows a diffusing reflector of the present invention. As illustrated in FIG. 1, a substrate 1, for example, consisting of glass material or the like. A resin film 2 having photosensitivity may be formed on the substrate 1, although this is not necessary. As a resin film 2, a photoresist, for example, may be used. In this embodiment, a film is formed in the thickness of about 1.0 $\mu$ m by coating of the photoresist with the spin coating or printing method. Next, in the process, a gathering of pillar-shaped bodies is provided as a film 3 by patterning the substrate or the resin film 2 with the nanoparticle metal suspension of the invention using spin-coating. Other processes such as photolithography may also be used. In the photolithography method, exposing process is

conducted through irradiation of ultraviolet ray and thereafter the developing process is performed. Adequate irradiation energy of ultraviolet ray is ranged from 150 mJ to 250 mJ. When irradiation energy is less than 150 mJ, the energy is too low and when it exceeds 250 mJ, the energy is too high, and thereby side etching may be generated. The metal film 3 is formed by depositing the nanoparticle metal material, for example, such as aluminum, silver or the like on the substrate 1 or the resin film 2 by spin-coating, sputtering, or vacuum evaporation.